

Data sheet acquired from Harris Semiconductor SCHS052B - Revised June 2003

# CMOS Analog Multiplexers/Demultiplexers

High-Voltage Types (20-Volt Rating)

CD4067B - Single 16-Channel

Multiplexer/Demultiplexer

CD4097B -Differential 8-Channel Multiplexer/Demultiplexer

### ■ CD4067B and CD4097B CMOS

analog multiplexers/demultiplexers\* are digitally controlled analog switches having low ON impedance, low OFF leakage current, and internal address decoding. In addition, the ON resistance is relatively constant over the full input-signal range.

The CD4067B is a 16-channel multiplexer with four binary control inputs, A,B,C,D, and an inhibit input, arranged so that any combination of the inputs selects one switch.

The CD4097B is a differential 8-channel multiplexer having three binary control inputs A, B, C, and an inhibit input. The inputs permit selection of one of eight pairs of switches.

A logic "1" present at the inhibit input turns all channels off.

The CD4067B and CD4097B types are supplied in 24-lead hermetic dual-in-line ceramic packages (F3A suffix), 24-lead dual-in-line plastic packages (E suffix), 24-lead small-outline packages (M, M96, and NSR suffixes), and 24-lead thin shrink small-outline packages (P and PWR suffixes).

When these devices are used as demultiplexers, the channel in/out terminals are the outputs and the common out/in terminals are the inputs.

#### Recommended Operating Conditions at TA = 25°C (Unless Otherwise Specified)

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges. Values shown apply to all types except as noted

Min. Characteristic Supply-Voltage Range (TA=Full Package-3 18 Temp. Range)

#### Multiplexer Switch Input 25 mΑ **Current Capability** Output Load Resistance $\cdot \Omega$

#### NOTE:

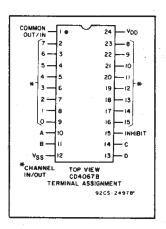
In certain applications, the external load-resistor current may include both VDD and signal-line components. To avoid drawing VDD current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from RON values shown in ELECTRICAL CHARAC-TERISTICS CHART). No VDD current will flow through RL if the switch current flows into terminal 1 on the CD4067; terminals 1 and 17 on the CD4097.

#### Features:

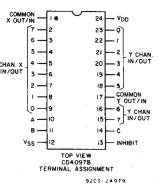
- Low ON resistance: 125  $\Omega$  (typ.) over 15  $V_{p-p}$  signal-input range for  $V_{DD}$  –  $V_{SS}$  = 15 V
- High OFF resistance: channel leakage of ±10 pA (typ.) @ VDD-VSS=10 V
- Matched switch characteristics: RoN=5  $\Omega$  (typ.) for VDD-VSS=15 V
- Very low quiescent power dissipation under all digital-control input and supply conditions: 0.2 μW (typ.) @ VDD-VSS=10 V
- Binary address decoding on chip
- 5-V, 10-V, and 15-V parametric ratings
- 100% tested for quiescent current at 20 V
- Standardized symmetrical output characteristics
- Maximum input current of 1 µA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- Meets all requirements of JEDEC Tentative Standard No. 138, "Standard Specifications for Description of 'B' Series CMOS Devices"

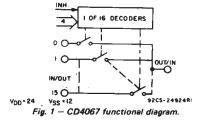
#### Applications:

- Analog and digital multiplexing and demultiplexing
- A/D and D/A conversion
- Signal gating



**CD4067B, CD4097B Types** 





# CD4067 TRUTH TABLE

A	В	С	D	Inh	Selected Channel
х	Х	х	Х	1	None
0	0	0	0	0	0
1	0	0	0	.0.	1 ,
0	1	0	0.	0	2
1	1	0	0	0	3
0	0	1	0	0	4 -
1	0	1	0	0	5
0	1	1	0	0	6
1	1	1	0	0	.7
0	0	0	1	0	8
1 1	0	0	1	0	9
0	1	0	1	0	10
1	1	0	1	0	11
0	0	1	1	0	12
1	0	1	1	0	13
0	1	1	1	0	14
1	1	1	1	0	15

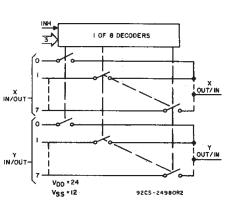


Fig. 2-CD4097 functional diagram.

#### CD4097 TRUTH TABLE

A	В	С	Inh	Selected Channel
х	х	Х	1	None
0	0	0	0	0X, 0Y
1	0	0	0	1X, 1Y
0	1	0	0	2X, 2Y
1	1	0	0	3X, 3Y
0	0	1	0	4X, 4Y
1	0	1	0	5X, 5Y
0	1	1	0	6X, 6Y
1	[ 1	1	0	7X, 7Y

#### **ELECTRICAL CHARACTERISTICS**

CHARAC- TERISTIC	(	CONDITIONS		LIMI	TS AT I	NDICAT	ED TEI	MPER/	ATURES	s (°C)	Units
	Vis	V <sub>SS</sub>	$V_{DD}$			+85	+125		+25		
0100101	(V)	(V)	(V)				L	Min.	Тур.	Max.	l
	015 (	V <sub>is</sub> ) AND OUT									
Quiescent			5	5	5	150	150		0.04	5	
Device Cur- rent, IDD			10	10	10	300	300	-	0.04	10	μA
Max.			15	20	20	600	600	- 1	0.04	20	-
ON-state Re			20	100	100	3000	3000		0.08	100	
sistance		2 4+4									
V <sub>SS</sub> ≤		0	5	800	850	1200	1300	·_	470	1050	
Vic≪VDD		0	10	310	330	520	550	-	180	400	÷ Ω
ron Max.	0	15	200	210	300	320		125	240		
Change in											
on-state	ĺ					ł	•	1			
Resistance (Between							100			1	
Any Two		0	5	_	_	_			15		
Channels)		0	10		_				. 10	<del>                                     </del>	Ω
$\Delta r_{on}$		0	15					_ :	5		1
OFF Chan-										1	
nel Leak-	İ								l	1.	
age Cur-											
rent: Any Channel									'		
OFF Max.										l	
or		0	18	±1	00*	±100	0*	-	±0.1	±100*	nΑ
All Chan-								1	ŀ		
nels OFF											
(Common OUT/IN)											
Max.											
Capacitance:							Γ	_			
Input, C <sub>is</sub>		i		_	-	-	-	-	5	-	
Output,		1								<u> </u>	1
Cos									l		
CD4067		-5	5	_		_		l	55	L	pF
CD4097					-	_	-	_	35		ام
Feed-											]
through,				_	_	-	-	-	0.2		
C <sub>ios</sub>											<u> </u>
Propaga-		R <sub>L</sub> = 200 KΩ	5	_	_	_		_	30	60	
tion Delay Time (Sig-	VDD	C <sub>L</sub> =50 pF	10	_	~		_		15	30	ns
nal Input		t <sub>r</sub> ,t <sub>f</sub> =20 ns	15	-		_		<b> </b>	10	20	
to Output		· .							'`	20	
CONTROL	(ADD	RESS or INHIB	T) V <sub>C</sub>		'		1,5-		- 8		
Input Low		R <sub>L</sub> =1 KΩ	5		1.5	i	<del></del>	Ι	—,	1.5	
Voltage,	}	to Vec	10		3		<del></del>	+			
Vill Max.	=VDD	I <sub>‡S</sub> <2 μA							<del>                                     </del>	3	1
- IL	thru	on all OFF	15		4			-	<u> </u>	4	
	1 KΩ	on all OFF	5	1	3.5	,		3.5	] –	-	
Input High	1.4	- Unanneis									
Input High Voltage, V <sub>IH</sub> Min.		Channels	10		7			7	_	-	

<sup>\*</sup> Determined by minimum feasible leakage measurement for automatic testing.

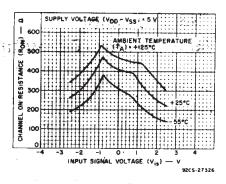


Fig. 3—Typical ON resistance vs. input signal voltage (all types).

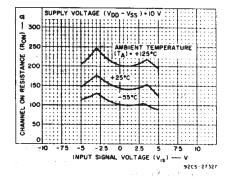


Fig. 4—Typical ON resistance vs. input signal voltage (all types).

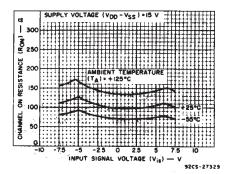


Fig. 5—Typical ON resistance vs. input signal voltage (all types).

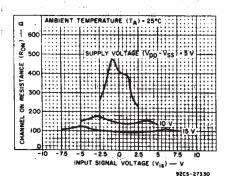
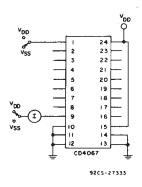


Fig. 6—Typical ON resistance vs. input signal voltage (all types).

#### **ELECTRICAL CHARACTERISTICS (Cont'd)**

CHARAC- TERISTIC	(	CONDITIONS				AT INI	DICATE		IPERATU	IRES	Units
	Vis	Vis VSS		-55	-40	+85	+125		+25		
	(V)	(V)	(V)					Min.	Тур.	Max.	
Input Current, I <sub>IN</sub> Max.	V <sub>IN</sub> =	0, 18 V	18	±0.1	±0.1	±1	±1		±10 <sup>-5</sup>	±0.1	μΑ
Propagation Delay Time: Address or		KΩ,C <sub>L</sub> = t <sub>r</sub> ,t <sub>f</sub> =20 ns									
Inhibit-to-		0	5	_				_	325	650	
Signal OUT (Channel		0	10		~	_	_	_	135	270	ns
turning ON)		0	15	-	_	_	-		95	190	1
Address or Inhibit-to-	R <sub>L</sub> =300 50 pF, 1	D Ω,C <sub>L</sub> = t <sub>r</sub> ,t <sub>f</sub> =20 ns									
Signal OUT		0	5	] _	_	→ .	-	~-	220	440	
(Channel turning		0	10	-	-			_	90	180	ns
OFF)		0	15	-		_	-	-	65	130	1
Input Capaci- tance, C <sub>IN</sub>	Any Ad Inhibit	ddress or Input			_	_	-	5	7.5	рF	

#### **TEST CIRCUITS**



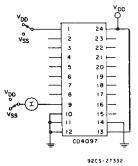


Fig. 7-OFF channel leakage current-any channel OFF.

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V <sub>DD</sub> )	
Voltages referenced to V <sub>SS</sub> Terminal)	
INPUT VOLTAGE RANGE, ALL INPUTS	0.5V to V <sub>DD</sub> +0.5V
DC INPUT CURRENT, ANY ONE INPUT	
POWER DISSIPATION PER PACKAGE (PD):	
For $T_A = -55^{\circ}C$ to $+100^{\circ}C$	500mW
For T <sub>A</sub> = +100°C to +125°C	. Derate Linearity at 12mW/OC to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Ty	pes)100mW
OPERATING-TEMPERATURE RANGE (TA)	
STORAGE TEMPERATURE RANGE (Tstg)	65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 inch (1.59 $\pm$ 0.79mm) from case for 10s max	+265°C

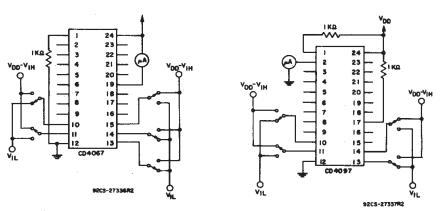


Fig. 8—Input voltage—measure  $\leq$  2  $\mu$ A on all OFF channels (e.g., channel 12).

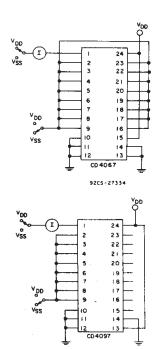
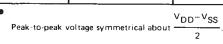


Fig. 9-OFF channel leakage current-all channels OFF.

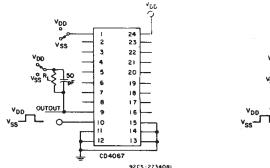
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# ELECTRICAL CHARACTERISTICS (Cont'd)

			TE	ST COND	ITIONS	-	· · · · · ·			
CHARAC- TERISTIC	V <sub>is</sub> (V)	V <sub>DD</sub> (V)	R <sub>L</sub> (ΚΩ)				TYPICAL VALUES	UNITS		
Cutoff	5 <b>°</b>	10	1							
(-3-dB) Frequency		.,		V at Co	mmon OUT/IN	CD4067	14	ŀ		
Channel ON	$20 \log \frac{V_{os}}{V_{is}} = -3 dB$					CD4097	20	MHz		
(Sine Wave Input)	20 109	'V <sub>is</sub>	3 00	V <sub>os</sub> at An	y Channel	60	IVIHZ			
Total	2.	5					0.3			
Harmonic	3 <b>•</b>	10	10				0.2			
Distortion, THD	5 <sup>•</sup>	15					0.12	%		
	f <sub>is</sub> = 1	k'Hz sine	wave					, i		
-40-dB	5 <b>•</b>	10	1							
Feedthrough		V		V at Co	mmon OUT/IN	CD4067 CD4097	20			
Frequency (All Channels	20 log	V <sub>os</sub>	10 dB			12	MHz			
OFF		Vis		V <sub>os</sub> at An	y Channel	8				
	5 <sup>•</sup>	10	1							
Signal Cross-				Between A	Any 2 Channels		1			
talk (Fre-	20.100	$\frac{V_{os}}{V_{is}} = -2$	10 4B	Between	Measured on Co	ommon	10			
quency at -40 dB)	20 log	Vis	Ю ССВ	Sections CD4097 Only	Measured on Ai Channel	ny	18	MHz		
		10	10*							
Address-or-		), t <sub>r</sub> ,t <sub>f</sub> =2								
Inhibit-to- Signal		DD-VS		,			75	mV (Peak)		
Crosstalk	oquar	re Wave)						(reak)		



- Worst case.
- \* Both ends of channel.



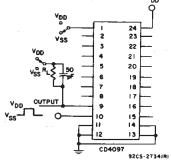


Fig. 11—Turn-on and turn-off propagation delay—address select input to signal output (e.g. measured on channel 0).

### TEST CIRCUITS (Cont'd)

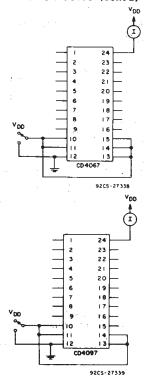
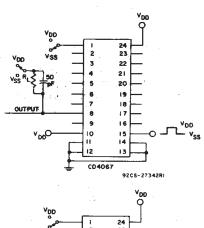


Fig. 10-Quiescent device current.



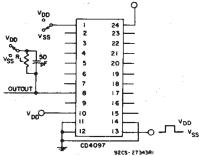
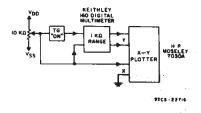
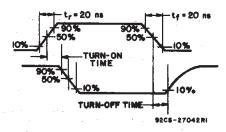


Fig. 12—Turn-on and turn-off propagation delay inhibit input to signal output (e.g. measured on channel 1).





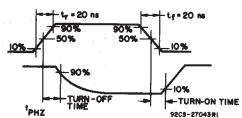


Fig. 13- Channel ON resistance measurement circuit.

Fig. 14— Propagation de/ay waveform channel being turned ON ( $R_L$  = 10 K  $\Omega$ ,  $C_L$  = 50 pF).

Fig. 15 — Propagation delay waveform, channel being turned OFF ( $R_L$  = 300  $\Omega$ ,  $C_L$  = 50 pF).

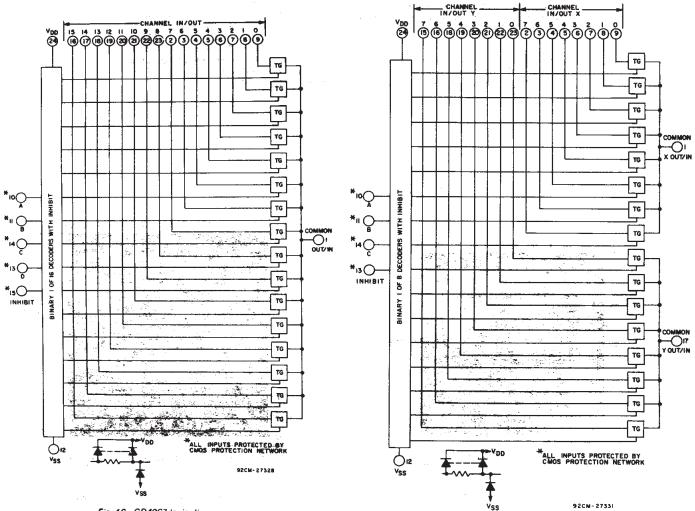


Fig. 16-CD4067 logic diagram.

Fig. 17-CD4097 logic diagram.

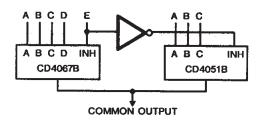


Fig. 18-24-to-1 MUX Addressing

#### SPECIAL CONSIDERATIONS

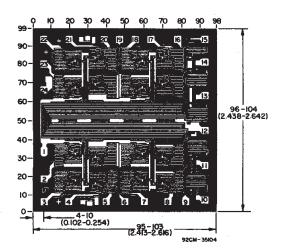
In applications where separate power sources are used to drive V<sub>DD</sub> and the signal inputs, the V<sub>DD</sub> current capability should exceed V<sub>DD</sub>/R<sub>L</sub> (R<sub>L</sub>=effective external load). This provision avoids permanent current flow or clamp action on the V<sub>DD</sub> supply when power is applied or removed from the CD4067B or CD4097B.

When switching from one address to another, some of the ON periods of the channels of the multiplexers will overlap momentarily, which may be objectionable in certain applications. Also when a channel is turned on or off by an address input, there is a momentary conductive path from the channel to VSS, which will dump some charge from any capacitor connected to the input or output of the channel. The inhibit input turning on a channel will similarly dump some charge to VSS.

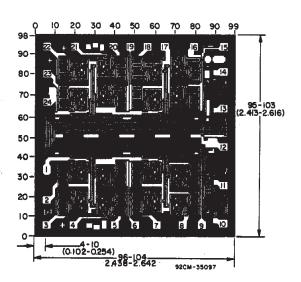
The amount of charge dumped is mostly a function of the signal level above VSS. Typically, at  $V_{DD}$ - $V_{SS}$ =10 V, a 100-pF

capacitor connected to the input or output of the channel will lose 3-4% of its voltage at the moment the channel turns on or off. This loss of voltage is essentially independent of the address or inhibit signal transition time, if the transition time is less than 1-2 µs. When the inhibit signal turns a channel off, there is no charge dumping to VSS. Rather, there is a slight rise in the channel voltage level (65 mV typ.) due to capacitive coupling from inhibit input to channel input or output. Address inputs also couple some voltage steps onto the channel signal levels.

In certain applications, the external load-resistor current may include both VDD and signal-line components. To avoid drawing VDD current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.8 volt (calculated from RON values shown in ELECTRICAL CHARACTERISTICS CHART). No VDD current will flow through RL if the switch current flows into terminal 1 on the CD4067B, terminals 1 and 17 on the CD4097B.



Dimensions and pad layout for CD4067BH.



Dimensions and pad layout for CD40978H.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils  $(10^{-3} \text{ inch})$ .

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### **PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CD4067BF	ACTIVE	CDIP	J	24	1	Non-RoHS & Non-Green	Call TI	N / A for Pkg Type	-55 to 125	CD4067BF	Samples
CD4067BF3A	ACTIVE	CDIP	J	24	1	Non-RoHS & Non-Green	Call TI	N / A for Pkg Type	-55 to 125	CD4067BF3A	Samples
CD4067BM	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4067BM	Samples
CD4067BM96	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-55 to 125	CD4067BM	Samples
CD4067BM96G4	ACTIVE	SOIC	DW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4067BM	Samples
CD4067BPW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM067B	Samples
CD4067BPWG4	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM067B	Samples
CD4067BPWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM067B	Samples
CD4097BF	ACTIVE	CDIP	J	24	1	Non-RoHS & Non-Green	Call TI	N / A for Pkg Type	-55 to 125	CD4097BF	Samples
CD4097BM	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4097BM	Samples
CD4097BME4	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4097BM	Samples
CD4097BMG4	ACTIVE	SOIC	DW	24	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CD4097BM	Samples
CD4097BPW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM097B	Samples
CD4097BPWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM097B	Samples
CD4097BPWRE4	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	CM097B	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

# PACKAGE OPTION ADDENDUM

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(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF CD4067B, CD4067B-MIL, CD4097B, CD4097B-MIL:

Catalog: CD4067B, CD4097B

Military: CD4067B-MIL, CD4097B-MIL

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

# **PACKAGE MATERIALS INFORMATION**

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# TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD4067BM96	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CD4067BM96G4	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CD4067BPWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1
CD4097BPWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1

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## \*All dimensions are nominal

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Device	Package Type	e Package Drawing		SPQ	Length (mm)	Width (mm)	Height (mm)	
CD4067BM96	SOIC	DW	24	2000	350.0	350.0	43.0	
CD4067BM96G4	SOIC	DW	24	2000	350.0	350.0	43.0	
CD4067BPWR	TSSOP	PW	24	2000	356.0	356.0	35.0	
CD4097BPWR	TSSOP	PW	24	2000	356.0	356.0	35.0	

# **PACKAGE MATERIALS INFORMATION**

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# **TUBE**



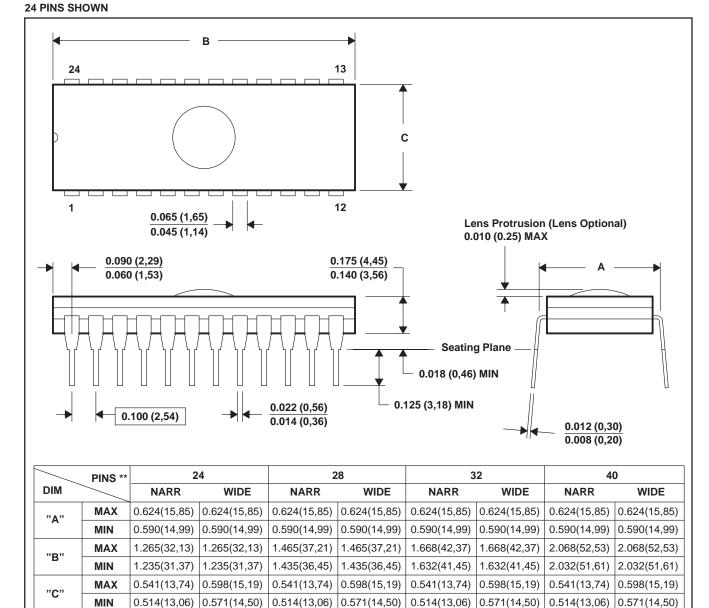
\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD4067BM	DW	SOIC	24	25	506.98	12.7	4826	6.6
CD4067BPW	PW	TSSOP	24	60	530	10.2	3600	3.5
CD4067BPWG4	PW	TSSOP	24	60	530	10.2	3600	3.5
CD4097BM	DW	SOIC	24	25	506.98	12.7	4826	6.6
CD4097BME4	DW	SOIC	24	25	506.98	12.7	4826	6.6
CD4097BMG4	DW	SOIC	24	25	506.98	12.7	4826	6.6
CD4097BPW	PW	TSSOP	24	60	530	10.2	3600	3.5

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### J (R-GDIP-T\*\*)

### **CERAMIC DUAL-IN-LINE PACKAGE**



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Window (lens) added to this group of packages (24-, 28-, 32-, 40-pin).
- D. This package can be hermetically sealed with a ceramic lid using glass frit.
- E. Index point is provided on cap for terminal identification.





SMALL OUTLINE PACKAGE



### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



DW (R-PDSO-G24)

# PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AD.



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